Logic level TOPFET

PIP3107-D

DESCRIPTION

Monolithic temperature and overload protected logic level power MOSFET in TOPFET2 technology assembled in a 3 pin surface mount plastic package.

APPLICATIONS

General purpose switch for driving

- lamps
- . motors
- solenoids
- heaters

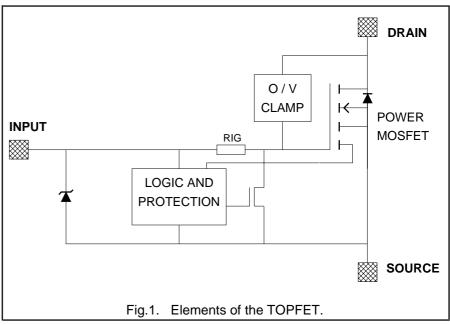
FEATURES

- TrenchMOS output stage Current limiting
- .
- Overload protection
- Overtemperature protection Protection latched reset by input .
- .
- 5 V logic compatible input level Control of output stage and . supply of overload protection circuits derived from input
- Low operating input current permits direct drive by micro-controller
- ESD protection on all pins
- Overvoltage clamping for turn off of inductive loads

QUICK REFERENCE DATA

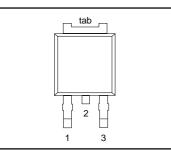
SYMBOL	PARAMETER	MAX.	UNIT	
V_{DS} I_{D} P_{D} T_{j} $R_{DS(ON)}$ I_{ISL}	Continuous drain source Continuous drain current Total power dissipation Continuous junction temp Drain-source on-state res Input supply current	erature	50 16 65 150 50 650	V A W °C mΩ μΑ
ISL	input supply current	V _{IS} – 3 V	000	μΑ

FUNCTIONAL BLOCK DIAGRAM



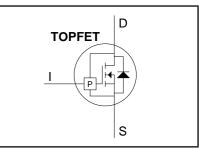
PINNING - SOT428

PIN	DESCRIPTION
1	input
2	drain
3	source
tab	drain



PIN CONFIGURATION

SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{DS}	Continuous drain source voltage ¹	-	-	50	V
I _D	Continuous drain current	$V_{IS} = 5 V; T_{mb} = 25 °C$	-	self -	А
				limited	
I _D	Continuous drain current	$V_{IS} = 5 V; T_{mb} \le 125 °C$	-	16	А
I,	Continuous input current	-	-5	5	mA
I _{IRM}	Non-repetitive peak input current	t _p ≤ 1 ms T _{mb} ≤ 25 °C	-10	10	mA
P _D	Total power dissipation	T _{mb} ≤ 25 °C	-	65	W
T _{stg}	Storage temperature	-	-55	175	°C
T	Continuous junction temperature ²	normal operation	-	150	°C
T_{sold}	Case temperature	during soldering	-	260	°C

ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _c	Electrostatic discharge capacitor voltage	Human body model; C = 250 pF; R = 1.5 k Ω	-	2	kV

OVERVOLTAGE CLAMPING LIMITING VALUES

At a drain source voltage above 50 V the power MOSFET is actively turned on to clamp overvoltage transients.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
E _{DSM} E _{DRM}	Inductive load turn-off Non-repetitive clamping energy Repetitive clamping energy	$ \begin{split} I_{\text{DM}} &= 16 \text{ A}; V_{\text{DD}} \leq 20 V \\ T_{\text{mb}} \leq 25 ^{\circ}\text{C} \\ T_{\text{mb}} \leq 95 ^{\circ}\text{C}; f = 250 \text{Hz} \end{split} $	-	200 32	mJ mJ

OVERLOAD PROTECTION LIMITING VALUE

With an adequate protection supply provided via the input pin, TOPFET can protect itself from two types of overload - overtemperature and short circuit load.

SYMBOL	PARAMETER	REQUIRED CONDITION	MIN.	MAX.	UNIT
V _{DS}	Drain source voltage ³	$4~V \leq V_{IS} \leq 5.5~V$	0	35	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance Junction to mounting base	-	-	1.75	1.92	K/W
R _{th j-a}	Junction to ambient	minimum footprint FR4 PCB	-	70	-	K/W

¹ Prior to the onset of overvoltage clamping. For voltages above this value, safe operation is limited by the overvoltage clamping energy.

 $[\]mathbf{2}$ A higher T_j is allowed as an overload condition but at the threshold $T_{j(TO)}$ the over temperature trip operates to protect the switch.

³ All control logic and protection functions are disabled during conduction of the source drain diode.

OUTPUT CHARACTERISTICS

Limits are for -40 $^\circ C \leq T_{mb} \leq$ 150 $^\circ C;$ typicals are for T_{mb} = 25 $^\circ C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Off-state	$V_{IS} = 0 V$				
V _{(CL)DSS}	Drain-source clamping voltage	I _D = 10 mA	50	-	-	V
		$I_{\text{DM}} = 2 \text{ A}; t_p \leq 300 \mu\text{s}; \delta \leq 0.01$	50	60	70	V
I _{DSS}	Drain source leakage current	$V_{DS} = 40 \text{ V}$ $T_{mb} = 25 \text{ °C}$	-	- 0.1	100 10	μΑ μΑ
	On-state	$I_{\text{DM}} = 6 \text{ A}; t_{p} \le 300 \mu\text{s}; \delta \le 0.01$				
R _{DS(ON)}	Drain-source resistance	$V_{IS} \geq 4.4 \text{ V}$ $T_{mb} = 25 \text{ °C}$ $V_{IS} \geq 4 \text{ V}$ $T_{mb} = 25 \text{ °C}$		- 36 - 39	95 50 100 55	mΩ mΩ mΩ mΩ

OVERLOAD CHARACTERISTICS

-40°C $\leq T_{mb} \leq$ 150°C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Short circuit load	V _{DS} = 13 V				
I _D	Drain current limiting		16 12	24 -	32 36	A A
		$4~V \leq V_{IS} \leq 5.5~V$	8	-	36	А
	Overload protection	$V_{IS} = 5 \text{ V}; T_{mb} = 25^{\circ} \text{C}$				
P _{D(TO)}	Overload power threshold	device trips if $P_D > P_{D(TO)}$	40	120	160	W
T _{DSC}	Characteristic time	which determines trip time ¹	200	350	600	μs
	Overtemperature protection					
T _{j(TO)}	Threshold junction temperature ²		150	170	-	°C

¹ Trip time $t_{d \, sc}$ varies with overload dissipation P_D according to the formula $t_{d \, sc} \approx T_{DSC}$ / In[P_D / $P_{D(TO)}$].

² This is independent of the dV/dt of input voltage V_{IS} .

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INPUT CHARACTERISTICS

The supply for the logic and overload protection is taken from the input. Limits are for -40°C $\leq T_{mb} \leq 150$ °C; typicals are for $T_{mb} = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
V _{IS(TO)}	Input threshold voltage	$V_{DS} = 5 \text{ V}; \text{ I}_{D} = 1 \text{ mA}$	T _{mb} = 25°C	0.6 1.1	- 1.6	2.4 2.1	V V
I _{IS}	Input supply current	normal operation;	$V_{IS} = 5 V$ $V_{IS} = 4 V$	100 80	220 195	400 330	μΑ μΑ
I _{ISL}	Input supply current	protection latched;	V _{IS} = 5 V V _{IS} = 3 V	200 130	400 250	650 430	μΑ μΑ
V _{ISR}	Protection reset voltage ¹	reset time $t_r \ge 100 \ \mu s$		1.5	2	2.9	V
t _{ir}	Latch reset time	$V_{IS1} = 5 V, V_{IS2} < 1 V$		10	40	100	μs
V _{(CL)IS}	Input clamping voltage	l _i = 1.5 mA		5.5	-	8.5	V
R _{IG}	Input series resistance ² to gate of power MOSFET		$T_{mb} = 25^{\circ}C$	-	33	-	kΩ

SWITCHING CHARACTERISTICS

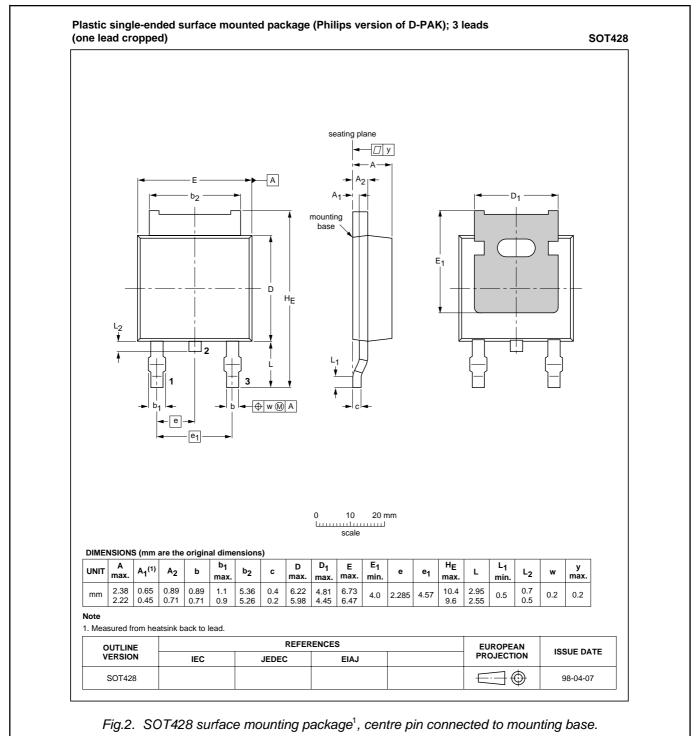
 T_{mb} = 25 °C; V_{DD} = 13 V; resistive load R_L = 4 Ω . Refer to waveform figure and test circuit.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t _{d on}	Turn-on delay time	$V_{IS} = 5 V$	-	15	30	μs
t,	Rise time		-	30	60	μs
t _{d off}	Turn-off delay time	$V_{IS} = 0 V$	-	70	140	μs
t _f	Fall time		-	35	70	μs

¹ The input voltage below which the overload protection circuits will be reset.

² Not directly measureable from device terminals.

MECHANICAL DATA



¹ Epoxy meets UL94 V0 at 1/8". Net mass: 1.1 g For soldering guidelines and SMD footprint design, please refer to Data Handbook SC18.

PIP3107-D

DEFINITIONS

DATA SHEET STA	TUS	
DATA SHEET STATUS ¹	PRODUCT STATUS ²	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product
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Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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¹ Please consult the most recently issued datasheet before initiating or completing a design.

² The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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